

Amendments to the Claims

Claim 1 (Original) A semiconductor device formed on a semiconductor substrate, said semiconductor device comprising:

an active region formed on the semiconductor substrate;
a dummy active region formed on the semiconductor substrate in a rectangular shape, wherein a length of a short side of said dummy active region is substantially no greater than 1 μ m and more than 0.5 μ m, wherein a distance between said active region and said dummy active region is greater than 0.5 μ m and less than 10 μ m; and
an isolation region formed on the semiconductor substrate and surrounding said active region and said dummy active region.

Claim 2 (Original) A semiconductor device according to claim 1, wherein said isolation region includes a trench filled with a high density plasma chemical vapor deposition layer.

Claim 3 (Original) A semiconductor device according to claim 2, wherein a depth of the trench is about 2500 \AA to 5000 \AA .

Claim 4 (Original) A semiconductor device according to claim 2, wherein the trench has a tapered shape.

Claim 5 (Original) A semiconductor device according to claim 2, wherein a taper angle of the trench is about 70 to 90 degrees.

Claim 6 (Original) A semiconductor device according to claim 2, wherein the high density plasma chemical vapor deposition layer is an oxide film.

Claim 7 (Currently Amended) A semiconductor device according to claim 6, wherein the oxide ~~file~~ film is abraded by Chemical Mechanical Polishing (CMP).

Claim 8 (Original) A semiconductor device according to claim 4, wherein a width of an opening of the trench is wider than a width of a bottom of the trench.

Claim 9 (Original) A semiconductor device according to claim 8, wherein the width of the opening of the trench is 0.5 to 1 μm .

Claim 10 (Currently Amended) A semiconductor device formed on a semiconductor substrate, said semiconductor device comprising:

an active region formed by the semiconductor substrate;

a dummy active region formed on the semiconductor substrate in a rectangular shape, wherein a length of a short side of said dummy active region is substantially no greater than 1 μm and more than 0.5 μm , wherein a distance between said active region and said dummy active region is greater than 0.5 μm and less than 10 μm ;

an isolation region formed on the semiconductor substrate and surrounding said active region and said dummy active region; and

a semiconductor element formed on said active region, said semiconductor element including a gate electrode formed over said active region, wherein a distance between said dummy active region and said gate electrode is more than 0.5 μm .

Claim 11 (Currently Amended) A semiconductor device according to claim 7-10, wherein said isolation region includes a trench filled with a high density plasma chemical vapor deposition layer.

Claim 12 (Original) A semiconductor device according to claim 11, wherein a depth of the trench is about 2500 \AA to 5000 \AA .

Claim 13 (Original) A semiconductor device according to claim 11, wherein the trench has a tapered shape.

Claim 14 (Original) A semiconductor device according to claim 11, wherein a taper angle of the trench is about 70 to 90 degrees.

Claim 15 **(Original)** A semiconductor device according to claim 11, wherein the high density plasma chemical vapor deposition layer is an oxide film.

Claim 16 **(Original)** A semiconductor device according to claim 15, wherein the oxide film is abraded by Chemical Mechanical Polishing (CMP).

Claim 17 **(Original)** A semiconductor device according to claim 13, wherein a width of an opening of the trench is wider than a width of a bottom of the trench.

Claim 18 **(Original)** A semiconductor device according to claim 17, wherein the width of the opening of the trench is 0.5 to 1 μm .